

CLAIMS

1. A structure comprising:  
a first conductor;  
a first isolation layer situated over said first conductor;  
5 a second conductor situated over said first isolation layer, said second conductor comprising under bump metal, said second conductor having at least one external pad;  
a second isolation layer situated over said second conductor, said second isolation layer having at least one hole over said at least one external pad of said second conductor;  
a bump attach site located at said at least one hole over said at least one external pad.
2. The structure of claim 1 wherein said under bump metal comprises material selected from the group consisting of copper and aluminum.
- 15 3. The structure of claim 1 wherein said first conductor is between approximately 2.0 microns and 5.0 microns thick.
4. The structure of claim 1 wherein said first isolation layer comprises at least one via.
- 20 5. The structure of claim 4 wherein said first conductor is connected to said second conductor through said at least one via so as to form an inductor.

6. The structure of claim 1 wherein said first conductor comprises interconnect metal.

5 7. The structure of claim 6 wherein said interconnect metal comprises material selected from the group consisting of copper and aluminum.

8. The structure of claim 7 wherein said first conductor is between approximately 1.0 micron and approximately 2.0 microns thick.

*SMR* 9. The structure of claim 1 wherein said first conductor is patterned from a layer of under bump metal.

10. The structure of claim 9 wherein said layer of under bump material comprises material selected from the group consisting of copper and aluminum.

*SMR* 11. The structure of claim 10 wherein said first conductor is between approximately 2.0 microns and approximately 5.0 microns thick.

20 12. The structure of claim 11 wherein said first and said second isolation layers comprise a dielectric.

13. The structure of claim 12 wherein said dielectric comprises a material selected from the group consisting of BCB and polyimide.

14. The structure of claim 12 wherein each of said first and said second isolation layers is between approximately 5.0 microns and approximately 10.0 microns thick.

15. The structure of claim 1 wherein said second conductor is situated substantially directly above said first conductor.

16. The structure of claim 15 wherein said first and said second conductors are cross-coupled so as to form a transformer.

17. A method for realizing passives, said method comprising steps of:  
15 fabricating a first conductor;  
forming a first isolation layer over said first conductor;  
fabricating a second conductor over said first isolation layer, said second conductor comprising under bump metal, said second conductor having at least one external pad;  
20 forming a second isolation layer over said second conductor, said second isolation layer having at least one hole over said at least one external pad of said second conductor;  
fabricating a bump attach site at said at least one hole over said at least one

external pad.

18. The method of claim 17 wherein said under bump metal comprises material selected from the group consisting of copper and aluminum.

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19. The method of claim 17 wherein said first conductor is between approximately 2.0 microns and 5.0 microns thick.

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20. The method of claim 17 further comprising a step of fabricating at least one via in said first isolation layer prior to said step of depositing said second isolation layer.

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21. The method of claim 20 further comprising a step of connecting said first conductor to said second conductor through said at least one via so as to form an inductor.

22. The method of claim 17 wherein said first conductor comprises interconnect metal.

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23. The method of claim 22 wherein said interconnect metal comprises material selected from the group consisting of copper and aluminum.

24. The method of claim 23 wherein said first conductor is between

approximately 1.0 micron and approximately 2.0 microns thick.

*Swish A/S*  
25. The method of claim 17 wherein said first conductor is patterned from a  
layer of under bump metal.

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26. The method of claim 25 wherein said layer of under bump metal comprises  
material selected from the group consisting of copper and aluminum.

*Swish A/S*  
27. The method of claim 26 wherein said first conductor is between  
approximately 2.0 microns and approximately 5.0 microns thick.

28. The method of claim 27 wherein said first and said second isolation layers  
comprise a dielectric.

15 29. The method of claim 28 wherein said dielectric comprises a material  
selected from the group consisting of BCB and polyimide.

30. The method of claim 17 wherein each of said first and said second isolation  
layers is between approximately 5.0 microns and approximately 10.0 microns thick.

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31. The method of claim 17 wherein said second conductor is fabricated  
substantially directly above said first conductor.

32. The structure of claim 31 wherein said first and said second conductors are cross-coupled so as to form a transformer.

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